## wave mechanics applied to semiconductor heterostructures

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## Contents

PREFACE	page	III
CHAPTER I : IDEALIZED QUANTUM WELLS AND SUPER- LATTICES. A SUMMARY	page	1
I. Single quantum wells		1
III. Tunnel coupling between wells: the symmetric double square		11
well		14
IV. Superlattices		18
IV.1. Superlattice dispersion relations		18
IV.2. Symmetry properties of the eigenfunctions		23
IV.3. Superlattice density of states		24
APPENDIX A : Symmetric double square well. Time-dependent aspect .		27
APPENDIX B : Dispersion relations of superlattices with arbitrary		
potential profiles		28
CHAPTER II : BAND STRUCTURE OF BULK III-V COMPOUNDS	page	31
I. Crystalline properties		31
II. Electronic properties		32
III. Electronic dispersion relations in the vicinity of the zone centre : k.p		
analysis and Kane model		35
III.1. k.p analysis and effective masses		36
III.2. Effective mass tensor. Electrons and holes		38
III.3. Beyond the quadratic dispersion relations : the Kane model		41
a) Dispersions relations of the Kane model		41
b) Band edge effective masses		45
c) Band non parabolicity		46
d) Inclusion of higher bands		46
e) Accuracy of the Kane model		47
IV. Conclusions		49
APPENDIX A : Inclusion of remote bands effects		50
APPENDIX B : Motion of Kane electrons in slowly varying perturbing		
fields		54

CHAPTER III: ENVELOPE FUNCTION DESCRIPTION OF HETE-		
ROSTRUCTURE ELECTRONIC STATES	page	63
I. Introduction		63
II. The envelope function model		64
II.1. Preliminaries		64
II.2. The envelope function framework		66
II.3. The Ben Daniel-Duke model		73
II.3.1. The Ben Daniel-Duke quantum wells $(m_A m_B > 0) \dots$		74
II.3.2. Interface states of Ben Daniel-Duke quantum wells		
$(m_{\rm A}m_{\rm B}<0\;;\;k_{\perp}=0)\;\ldots$		79
II.4. Quantum wells and superlattices with hosts which display		
Kane-like bands		83
II.5. Simplified calculations of superlattices and quantum wells		
states $k_{\perp} = 0$		88
II.6. Miscelleanous limiting cases		89
II.6.1. Evanescent propagation in one kind of layer. Quantum		
well bound states		89
II.6.2. Tight-binding expansion of the superlattice states		90
II.6.3. Propagating states in both kinds of layers		91
II.6.4. Heavy hole superlattice states		92
II.7. Specific examples		93
II.8. Labelling and counting superlattice states		100
III. In-plane dispersions in semiconductor heterostructures		101
APPENDIX A : Boundary conditions and stationary states		112
APPENDIX B : Coupling between light and heavy particle states due		
to inversion asymmetry splitting in bulk materials.		
Qualitative aspects		113
CHAPTER IV : COULOMBIC BOUND STATES AND INTERFACE DEFECTS IN HETEROSTRUCTURES	page	119
Coulombic bound states		

1.	Qualitative aspects	119
	I.1. Bulk hydrogenic impurities	119
	I.2. Impurities in heterostructures	120
п.	Approximate solutions of the hydrogenic impurity problem	121
	II.1. Formulation of the problem	121
	II.2. Results for the ground impurity state attached to the ground	
	subband	123
	II.3. Excited subbands. Continuum	125
	II.4. Excited impurity levels attached to the ground subband	127
	II.5. Acceptor levels in a quantum well	128

VI

C-	104.5	
co	nte	nts

VII

III. Excitons	128
III.1. Excitons in idealized bulk materials	130
III.2. Excitons in idealized quantum well structures	132
III 3 Excitons in actual quantum well structures	139
Interface defects	157
Interface defects	
I. Graded interfaces	142
II. Quantum well interface defects	143
III. Superlattice defect states	149
APPENDIX : Energy levels in a quantum well with narrow graded	
interfaces	151
CHAPTER V : ENERGY LEVELS IN MODULATION-DOPED	
HETEROSTRUCTURES	page 155
I The modulation domine of hotorolymoticne. Qualitative generate	155
1. The modulation doping of neterojunctions. Qualitative aspects	155
1.1. The unperturbed heterojunction (flat band case)	150
1.2. Single heterojunction containing diluted Coulombic impurities .	157
I.3. Actual heterostructures II. Self consistent calculations of energy levels and charge transfer in	160
single heterojunctions	161
II.1. Energy level calculations	165
II 2. Charge transfer in single heterojunctions	172
III. Energy levels in modulation-doped quantum wells	180
APPENDIX A · The algebra of the modified Fang Howard wave-	
function	186
APPENDIX B : Heteroiunction energy levels : qualitative aspects	188
The Decision of the terms of terms	100
CHARTER VI - ELECTRICAL CONDUCTIVITY OF OUASI BL	
DIMENSIONAL ELECTRON CASES	nage 193
	page 175
I. Static conductivity of a quasi bi-dimensional electron gas	194
I.1. Electrical conductivity in the electric quantum limit	199
I.2. Intersubband scattering	200
I.3. Screening in a quasi bi-dimensional electron gas. Application	
to Coulombic impurities	204
I.4. Discussion of the dielectric function	207
II. Evaluation of some scattering mechanisms	212
II.1. Mobility limited by Coulombic scattering	212
II.2. Alloy scattering	219
II.3. Interface roughness scattering	223
III. Vertical transport	225
IV. Resonant tunnelling	228
APPENDIX : Dimensional dependence of the screening effects	233

VIII Wave mechanics applied to semiconductor heterostructures

CHAPTER VII : OPTICAL PROPERTIES OF QUASI BI-DIMEN-	227
SIUNAL SISIEMS	page 237
I. Absorption (one-electron approximation)	237
I.1. Intraband transitions	243
I.2. Interband transitions	246
I.2.1. Polarization selection rules	247
I.2.2. Selection rules on the envelope function quantum num-	
bers : evaluation of $\langle f_i/f_f \rangle$	247
I.2.3. Order of magnitude of the absorption coefficient. Com-	
parison between type I and type II systems	251
I.2.4. Interband optical transitions in superlattices	255
II. Absorption : a simplified description of excitonic effects	258
II.1. Absorption in the absence of Coulombic interactions. Equi-	
valence with the one-electron model	260
II.2. Absorption in the presence of electron-electron interactions	262
III. Photoluminescence of quasi bi-dimensional systems	272
III.1. Introduction	272
III.2. Quantum well luminescence (steady state)	281
III.2.1. Band to band emission	282
III.2.2. Excitonic recombination	289
111.2.3. Extrinsic photoiuminescence	295
CHAPTER VIII : EFFECT OF STATIC EXTERNAL ELECTRIC AND MAGNETIC FIELDS ON THE ENERGY LEVELS OF QUASI BI-DIMENSIONAL ELEC- TRON GASES	<b>page</b> 303
	202
1. The Stark effects	303
1.1. Fransverse Stark effect in a quantum well $(F//x)$	209
I.2. Longitudinal Stark effect in a quantum well $(F//2)$	217
II. Lunau quantization of a quasi bi-almensional electron gas	317
II.2 Magnetic field dependent density of states	325
II.3. Magnetoconductivity of a quasi bi-dimensional electron gas	329
II.3.1. Macroscopic derivation	329
II.3.2. Microscopic discussion	332
II.4. Cyclotron resonance	339
ADDENIDIV A : Motion of three dimensional electrons in crossed elec	
ATTENDIX A . Motion of intee-almensional electrons in crossed elec-	
tric and magnetic fields	345
tric and magnetic fields	345
tric and magnetic fields   AI. The Drude model   AIL Output motion of hulk electrons in a magnetic field	345 346
tric and magnetic fields   AI. The Drude model   AII. Quantum motion of bulk electrons in a magnetic field	345 346 348
tric and magnetic fields   AI. The Drude model   AII. Quantum motion of bulk electrons in a magnetic field	345 346 348